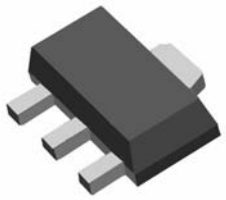
BC869 TRANSISTOR (PNP)

SOT-89

1. BASE
2. COLLECTO
3. EMITTER



FEATURES

Power dissipation

$P_{CM:}$ 500 mW (Tamb=25℃)

Collector current

$I_{CM:}$ -2 A

Collector-base voltage

$V_{(BR)CBO:}$ -32 V

Operating and storage junction temperature range

T_J, T_{stg}: -65℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-0.1mA, I_E=0	-32		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1mA , I_B=0	-20		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.1mA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}=-25V, I_E=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0		-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-10V, I_C= -5mA V_{CE}=-1V, I_C= -500mA V_{CE}=-1V, I_C= -1A	50 100 60	375	
BC869-16 **BC869-25**	$h_{FE(2)}$	V_{CE}=-1V, I_C= -500mA	100 160	250 375	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-1A, I_B= -100mA		0.5	V
Transition frequency	f_T	V_{CE}=-5V, I_C=-10mA f = 100MHz	40		MHz

DEVICE MARKING	**BC869**=CEC **BC869-16**=CGC **BC869-25**=CHC